



BG2,BG3,BG4

GLASS PASSIVATED SILICON FAST RECOVERY DIODE

Features:

1. Silicon diffusion mesa.
2. Glass Passivated package.
3. Small volume, light weight.
4. Small high-temperature leakage.
5. Good thermal stability.
6. High reliability.
7. Implementation of standards: GJB33A-97, QZJ840611A, QZJ840611



TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

Parameter name	Symbols	Unit	Specifications			Test Condition
			BG2	BG3	BG4	
Use for	High-frequency, switch circuit.					
Store temperature	T	$^\circ\text{C}$	-55~+150			
Quality Class			JP, JT, JCT, GS, G, G+			
Peak Repetitive Reverse Voltage	V_{RRM}	V	50~1400			
Average Forward Current	$I_{F(AV)}$	A	1.0	2.0	3.0	
Peak Forward Voltage	V_{FM}	V	2.4/1A	2.4/2A	A~F:2.2/3A G~J:2.6/3A	$I=I_{F(AV)}$
Average Forward Voltage	V_F	V	1.2	1.2	A~F:1.2 G~J:1.5	$I=I_{F(AV)}$
Non-repeat Forward Surge Current	I_{FSM}	A	20	40	50	Single-phase industrial frequency sine half wave 10ms
Peak Reverse Current	I_{RM1}	μA	10			$V_R=V_{RRM}, T_a=25^\circ\text{C}$
Peak Reverse Current	I_{RM2}	μA	200			$V_R=V_{RRM}, T_a=125^\circ\text{C}$
Junction Temperature	T_{jm}	$^\circ\text{C}$	150			
Reverse Recovery Time	t_{rr}	μS	1			$V_R=10\text{V}, I_F=50\text{mA}, R_L=75\text{ohms}$

SPECIFICATIONS:

A	B	C	D	E	F	G	H	I	J
50V	100V	200V	300V	400V	600V	800V	1000V	1200V	1400V

Outline and Dimensions:

Model cross: BG3(BZG2), BG4(BZG3)